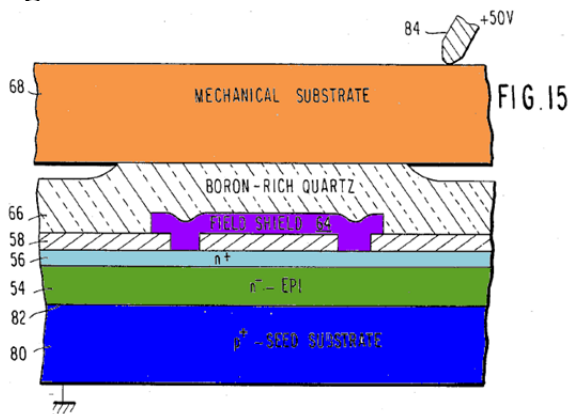


Claim 9

The method of claim 1, further including an additional step, after the step of attaching and before the step of etching, of fixing the second substrate to an etching support that is resistant to attack by an etchant.

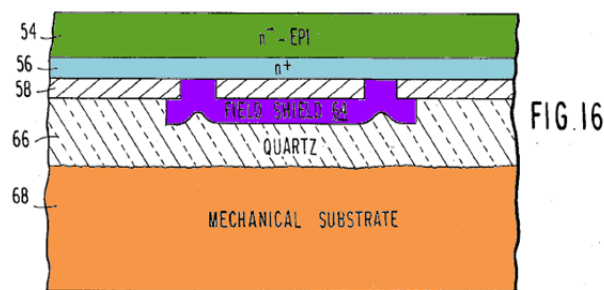
“The mechanical substrate 68 of silicon is then anodically bonded to the quartz 66 by applying voltage to a voltage probe 84 with the seed substrate 80 grounded.” **Cade, 7:27-30.**

Figure 15 of Cade



“The etch-back of the seed substrate 80 is performed with hydrofluoric-nitric-acetic acid (HNA) in the proportions of 1:3:8. The etchant HNA is an isotropic etch and attacks heavily doped p+ or n+ silicon. However, it does not appreciably attack silicon doped below the level of 10^{18} /cm³. The etch stopping characteristics are improved by the p+ /n junction at the interface 82.” **Cade, 7:31-37.**

Figure 16 of Cade



“In co-planar lapping the wafers are normally waxed to a plano, circular disk giving greater protection to the wafer.” **Soper, at 415.**

Figure 2 of Soper, at 418.

silicon sub-
strates.

